TC5588P/J-15,-20,-25,-35

8,192 WORD × 8 BIT CMOS STATIC RAM

DESCRIPTION

The TC5588P/J is a 65,536 bits high speed static random access memory organized as 8,192 words by 8 bits using CMOS technology, and operated from a single 5-volt supply. Toshiba's CMOS technology and advanced circuit from provides high speed feature.

The TC5588P/J has low power feature with device control using Chip Enable ($\overline{CE1}$/CE2), and has Output Enable Input ($\overline{OE}$) for fast memory access. Also the device power at memory access is reduced by automatic power down circuit form.

The TC5588P/J is suitable for use in cache memory where high speed is required, and high speed storage. All Inputs and Outputs are directly TTL compatible.

The TC5588P/J is moulded in 28 pin standard DIP and SOJ with 300 mil width for high density surface assembly.

FEATURES

- Fast access time:

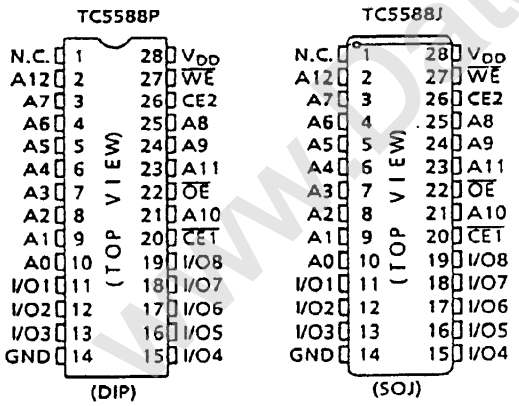
TC5588P/J-15	15ns (MAX.)
TC5588P/J-20	20ns (MAX.)
TC5588P/J-25	25ns (MAX.)
TC5588P/J-35	35ns (MAX.)

- Low power dissipation:

Operation	TC5588P/J-15	135mA (MAX.)
	TC5588P/J-20	115mA (MAX.)
	TC5588P/J-25	115mA (MAX.)
	TC5588P/J-35	115mA (MAX.)
Standby		1mA (MAX.)

- 5V single power supply : 5V±10%
- Fully static operation
- Directly TTL compatible : All Input and Output
- Output buffer control : $\overline{OE}$
- Package
  TC5588P : DIP28-P-300B
  TC5588J : SOJ28-P-300A

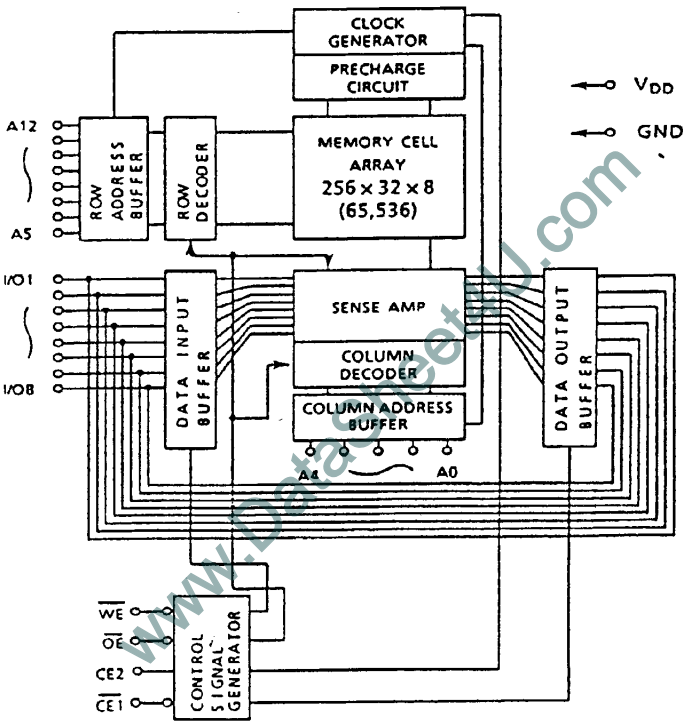
PIN CONNECTION



PIN NAMES

A0~A12	Address Inputs
I/O1~I/O8	Data Inputs/Outputs
$\overline{CE1}$, CE2	Chip Enable Inputs
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
V_{DD}	Power (+5V)
GND	Ground
N.C.	No Connection

BLOCK DIAGRAM



AXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT
V_{DD}	Power Supply Voltage	−0.5~7.0	V
V_{IN}	Input Voltage	−2.0~7.0	V
V_{OUT}	Output Voltage	−0.5~V_{DD} + 0.5	V
P_D	Power Dissipation	1.0	W
Tsolder	Soldering Temperature · Time	260 · 10	°C · sec
Tstrg	Storage Temperature	−65~150	°C
Topr	Operating Temperature	-10~85	°C

C RECOMMENDED OPERATING CONDITIONS (Ta = 0~70°C)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V_{DD}	Power Supply Voltage	4.5	5.0	5.5	V
V_{IH}	Input High Voltage	2.2	−	V_{DD} + 0.5	V
V_{IL}	Input Low Voltage	*−3.0	−	0.8	V

* Pulse width ≦ 10ns, DC : −0.5V (min)

C CHARACTERISTICS (Ta = 0~70°C, V_{DD} = 5V ± 10%)

SYMBOL	PARAMETER	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
I_{IL}	Input Leakage Current	V_{IN} = 0~V_{DD}		−	−	±1	μA
I_{OH}	Output High Current	V_{OH} = 2.4V		−4	−	−	mA
I_{OL}	Output Low Current	V_{OL} = 0.4V		8	−	−	mA
I_{LO}	Output Leakage Current	$\overline{CE1}$ = V_{IH} or CE2 = V_{IL} or $\overline{WE}$ = V_{IL} or $\overline{OE}$ = V_{IH}, V_{OUT} = 0~V_{DD}		−	−	±1	μA
I_{DDO}	Operating Current	V_{DD} = 5.5V tcycle = Min cycle $\overline{CE1}$ = V_{IL} and CE2 = V_{IH} Other Inputs = V_{IH}/V_{IL} I_{OUT} = 0mA	−15	−	−	135	mA
			−20				
			−25	−	−	115	
			−35				
I_{DDS1}	Standby Current	V_{DD} = 5.5V tcycle = Min cycle $\overline{CE1}$ = V_{IH} or CE2 = V_{IL} Other Inputs = V_{IH}/V_{IL}		−	−	25	mA
I_{DDS2}*		$\overline{CE1}$ = V_{DD} − 0.2V or CE2 = 0.2V Other Inputs = V_{DD} − 0.2V or 0.2V		−	−	1	

*: In standby mode with $\overline{CE1} \geqq V_{DD} - 0.2V$, these specification limits are guaranteed under the condition of $\overline{CE2} \geqq V_{DD} - 0.2V$ or $CE2 \leqq 0.2V$.

CAPACITANCE (Ta = 25°C, f = 1.0MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX.	UNIT
C_{IN}	Input Capacitance	V_{IN} = GND	5	pF
C_{OUT}	Output Capacitance	V_{OUT} = GND	7	pF

NOTE : This parameter periodically sampled is not 100% tested.

AC CHARACTERISTICS ($Ta = 0 \sim 70°C$ (1), $V_{DD} = 5V \pm 10\%$)

READ CYCLE

SYMBOL	PARAMETER	TC5588P/J-15		TC5588P/J-20		TC5588P/J-25		TC5588P/J-35		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
t_{RC}	Read Cycle Time	15	–	20	–	25	–	35	–	ns
t_{ACC}	Address Access Time	–	15	–	20	–	25	–	35	
t_{CO1}	$\overline{CE1}$ Access Time	–	15	–	20	–	25	–	35	
t_{CO2}	CE2 Access Time	–	15	–	20	–	25	–	35	
t_{OE}	$\overline{OE}$ Access Time	–	9	–	10	–	12	–	12	
t_{OH}	Output Data Hold Time From Address Change	5	–	5	–	5	–	5	–	
t_{COE}	Output Enable Time from $\overline{CE1}$ or CE2	5	–	5	–	5	–	5	–	
t_{COD}	Output Disable Time from $\overline{CE1}$ or CE2	–	6	–	6	–	6	–	6	
t_{OEE}	Output Enable Time from $\overline{OE}$	0	–	0	–	0	–	0	–	
t_{ODO}	Output Disable Time from $\overline{OE}$	–	5	–	5	–	5	–	5	
t_{PU}	Chip Selection to Power Up Time	0	–	0	–	0	–	0	–	
t_{PD}	Chip Deselection to Power Down Time	–	15	–	20	–	25	–	35	

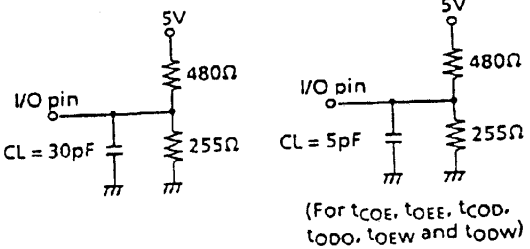
WRITE CYCLE

SYMBOL	PARAMETER	TC5588P/J-15		TC5588P/J-20		TC5588P/J-25		TC5588P/J-35		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
t_{WC}	Write Cycle Time	15	–	20	–	25	–	35	–	ns
t_{CW}	Chip Enable to End of Write	12	–	13	–	15	–	15	–	
t_{AS}	Address Set Up Time	0	–	0	–	0	–	0	–	
t_{WP}	Write Pulse Width	12	–	13	–	15	–	15	–	
t_{WR}	Write Recovery Time	0	–	0	–	0	–	0	–	
t_{DS}	Data Set Up Time	9	–	10	–	12	–	12	–	
t_{DH}	Data Hold Time	0	–	0	–	0	–	0	–	
t_{OEW}	Output Enable Time from $\overline{WE}$	0	–	0	–	0	–	0	–	
t_{ODW}	Output Disable Time from $\overline{WE}$	–	6	–	6	–	6	–	6	

AC TEST CONDITIONS

Input Pulse Levels	3.0V/0.0V
Input Pulse Rise and Fall Time	3ns
Input Timing Measurement Reference Levels	2.2V/0.8V
Output Timing Measurement Reference Levels	2.0V/0.8V
Output Load	Fig. 1

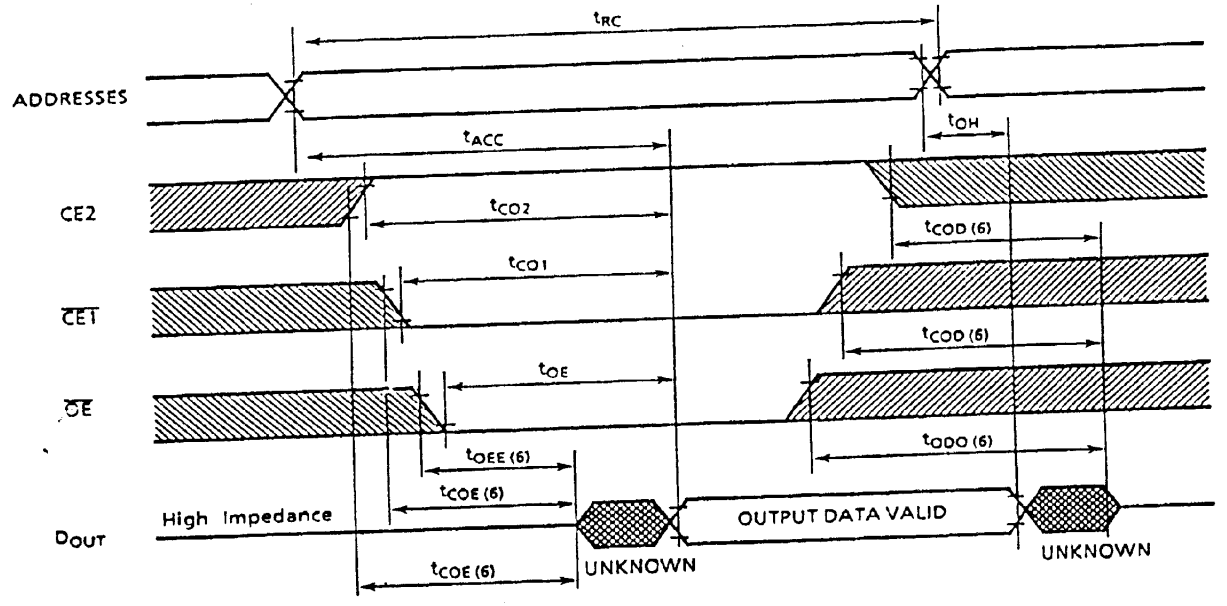
Fig. 1



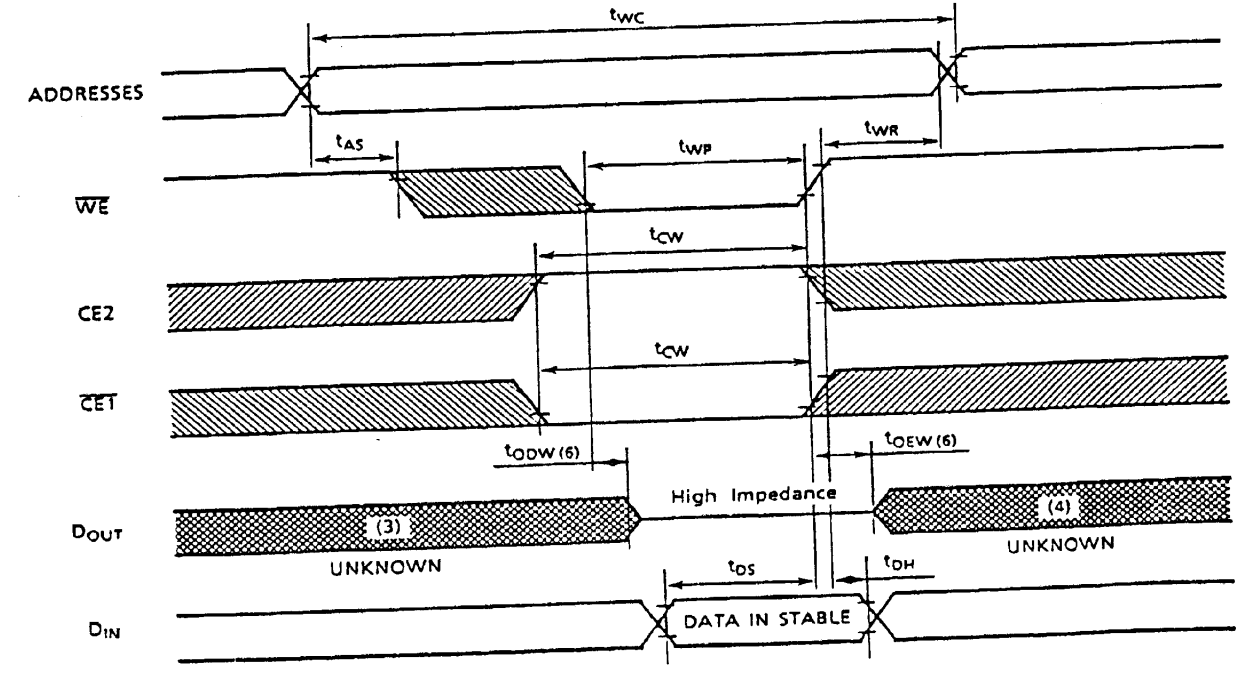
(For t_{COE}, t_{OEE}, t_{COD}, t_{ODO}, t_{OEW} and t_{ODW})

TIMING WAVEFORMS

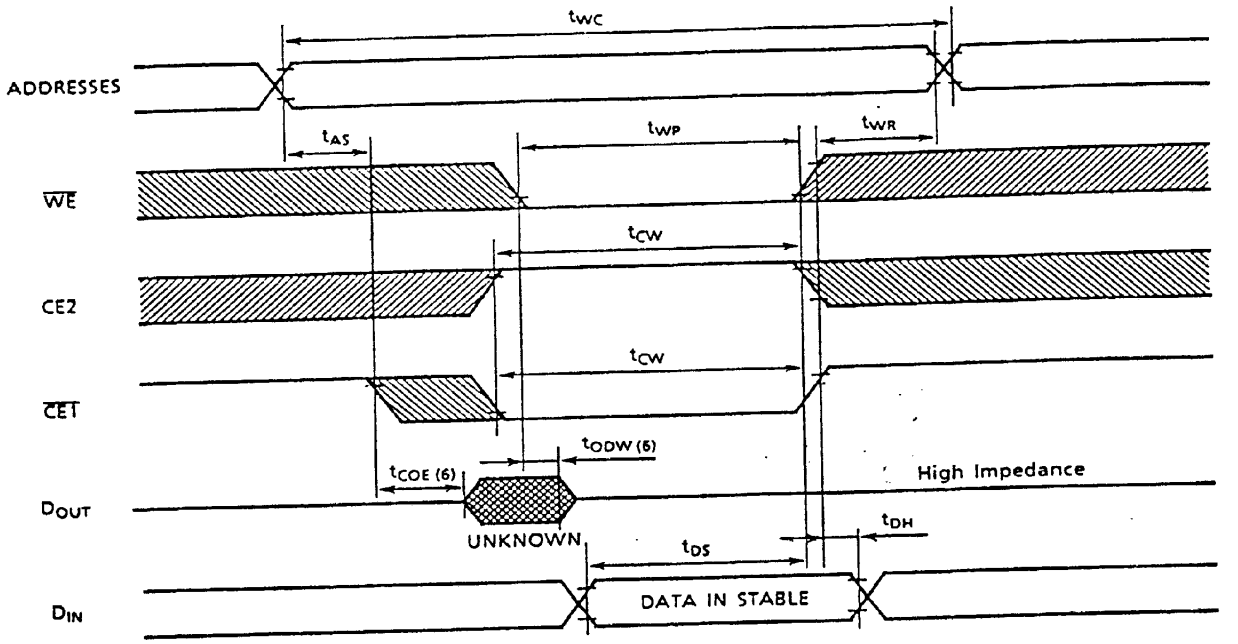
READ CYCLE (2)



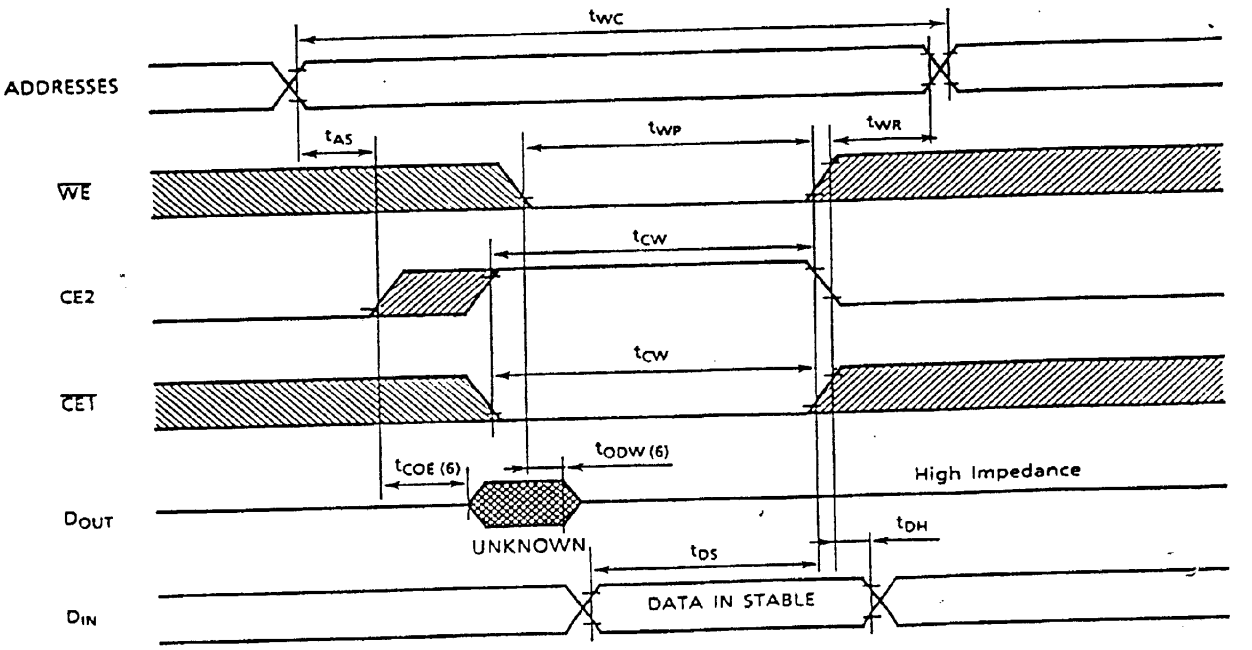
WRITE CYCLE 1 (5) ($\overline{WE}$ Controlled Write)



WRITE CYCLE 2 (5) ($\overline{CE1}$ Controlled Write)



WRITE CYLCE 3 (5) (CE2 Controlled Write)



NOTES: 1. The operating temperature (Ta) is guaranteed with transverse air flow exceeding 400 linear feet per minute.

2. $\overline{WE}$ is High for Read Cycle.

3. Assuming that $\overline{CE1}$ Low transition or CE2 High t **ransi** tion occurs coincident with or **after** $\overline{WE}$ Low transition, Outputs remain in a high impedance state.

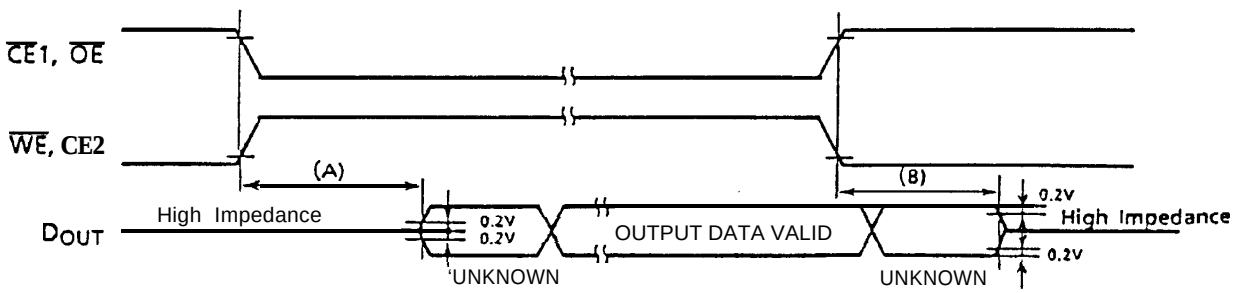
4. Assuming that $\overline{CE1}$ High transition **or** CE2 Low transition occurs coincident with or **prior** to $\overline{WE}$ High transition, Outputs remain in a high impedance state.

5. Assuming that $\overline{OE}$ is High for Write Cycle, Outputs are in a high impedance state **during** this period.

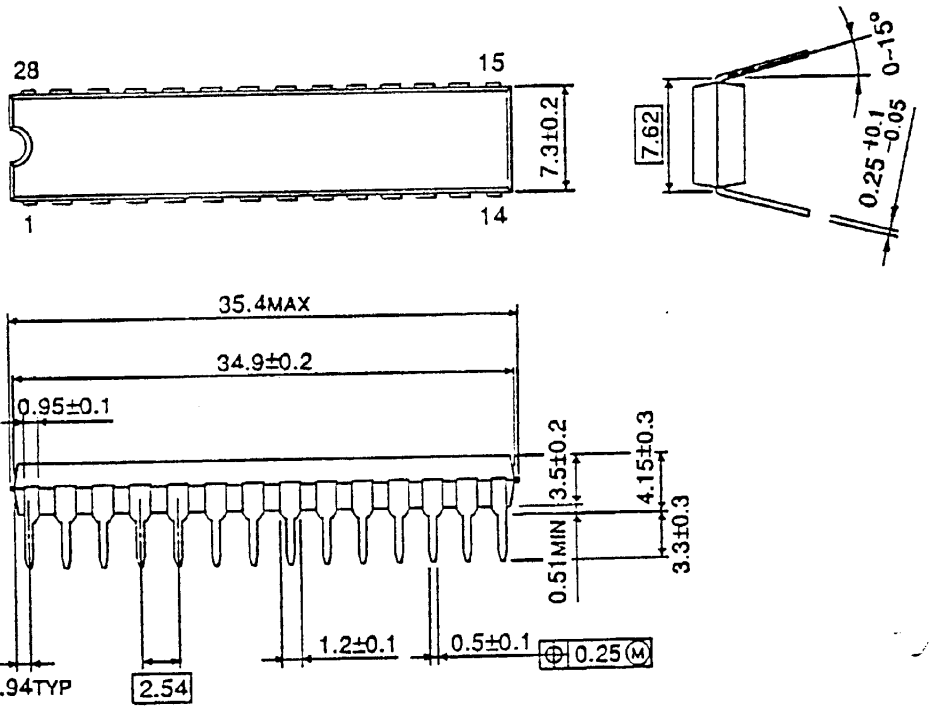
6. These Parameters are specified as **follows** and measured by using the Ioad shown **in Fig. 1.**

   (A) t_{COE}, t_{OEE}, t_{OEW} ····· Output Enable Time

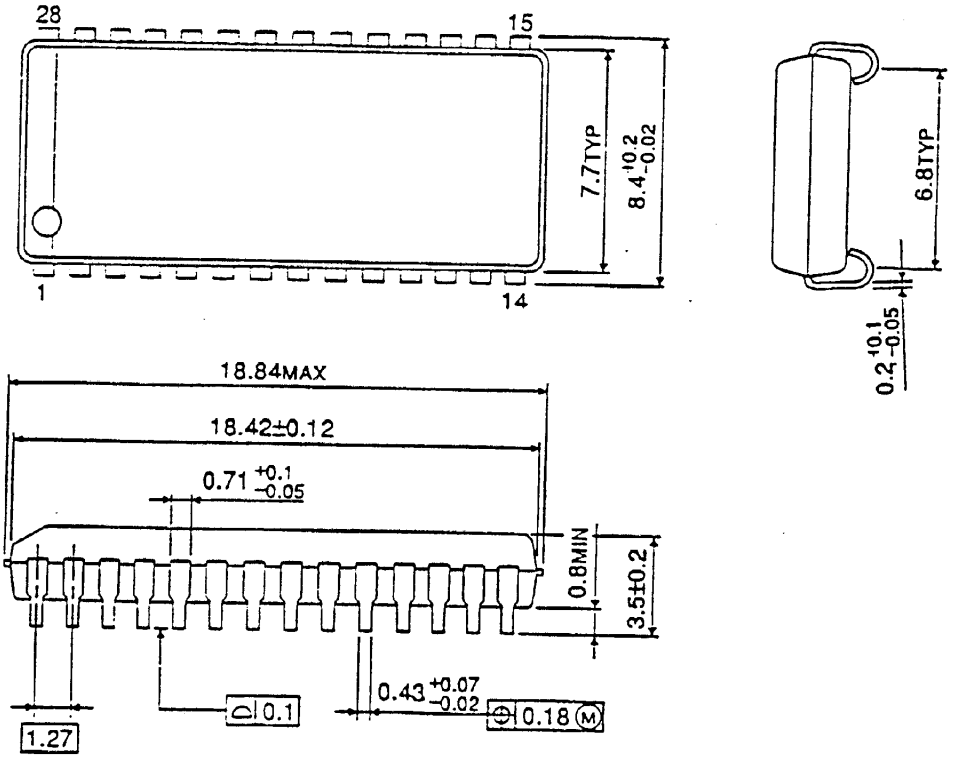
   (B) t_{COD}, t_{ODO}, t_{ODW} ····· Output Disable Time



DIP28-P-300B


28
15
1
14
7.3±0.2
7.62
0~15°
0.25 +0.1 -0.05
35.4MAX
34.9±0.2
0.95±0.1
3.5±0.2
4.15±0.3
3.3±0.3
0.51MIN
1.2±0.1
0.5±0.1
0.25 M
0.94TYP
2.54

SOJ28-P-300A


28
15
1
14
7.7TYP
8.4 +0.2 −0.02
6.8TYP
0.2 +0.1 −0.05
18.84MAX
18.42±0.12
0.71 +0.1 −0.05
0.8MIN
3.5±0.2
1.27
0.1
0.43 +0.07 −0.02
0.18 M